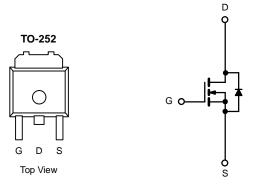


4904NG-VB Datasheet N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A) ^{a, e}	Q _g (Typ)			
30	0.002 at V _{GS} = 10 V	100	72 nC			
30	0.003 at V _{GS} = 4.5 V	90	72110			



N-Channel MOSFET

FEATURES

- Trench Power MOSFET
- 100 % R_q and UIS Tested
- Compliant to RoHS Directive 2011/65/EU



APPLICATIONS

- OR-ing
- Server
- DC/DC

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	30	V	
Gate-Source Voltage		V _{GS}	± 20	v	
	T _C = 25 °C		100 ^{a, e}		
Continuous Drain Current (T ₁ = 175 °C)	T _C = 70 °C		80 ^e		
Continuous Diam Current (1 j = 173 C)	T _A = 25 °C	I _D	35.8 ^{b, c}	A	
	T _A = 70 °C		27 ^{b, c}	_ ^	
Pulsed Drain Current		I _{DM}	300	7	
Avalanche Current Pulse		I _{AS}	39		
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	94.8	mJ	
Continuous Source-Drain Diode Current	T _C = 25 °C	L-	90 ^{a, e}	Λ.	
Continuous Source-Diam Diode Current	T _A = 25 °C	l _s —	3.13 ^{b, c}	A	
	T _C = 25 °C		235 ^a		
Manipular Davier Dissipation	T _C = 70 °C	ь	165	10/	
Maximum Power Dissipation	T _A = 25 °C	P _D	3.75 ^{b, c}	W	
	T _A = 70 °C		2.63 ^{b, c}		
Operating Junction and Storage Temperature Ra	T _J , T _{stq}	- 55 to 175	°C		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Тур.	Max.	Unit	
Maximum Junction-to-Ambient ^{b, d}	t ≤ 10 sec	R_{thJA}	32	40	°C/W	
Maximum Junction-to-Case	Steady State	R _{thJC}	0.5	0.6	C/VV	

Notes:

- a. Based on T_C = 25 °C.
 b. Surface mounted on 1" x 1" FR4 board.

- b. Striate informed on 1 X 1 114 board.
 c. t = 10 sec.
 d. Maximum under steady state conditions is 90 °C/W.
 e. Calculated based on maximum junction temperature. Package limitation current is 90 A.



SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)							
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static	Ţ			1	ı		
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V, I}_{D} = 250 \mu\text{A}$	30			V	
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I _D = 250 μA		35		mV/°(
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 7.5			
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1.5		2.5	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current	l	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$			1	μA	
Zero Gate voltage Drain Current	IDSS	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 \text{ °C}$			10		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	90			Α	
D : 0	D	V _{GS} = 10 V, I _D = 38.8 A		0.002			
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 37 \text{ A}$		0.003		Ω	
Forward Transconductance ^a	g _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 38.8 \text{ A}$		160		S	
Dynamic ^b							
Input Capacitance	C _{iss}			5201		pF	
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		1525			
Reverse Transfer Capacitance	C _{rss}			770			
T. 10 (0)	0	V _{DS} = 15 V, V _{GS} = 10 V, I _D = 38.8 A		151	227	nC	
Total Gate Charge	Q_g	30 30 2		71.5	103		
Gate-Source Charge	Q_{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 28.8 \text{ A}$		30			
Gate-Drain Charge	Q_{gd}			24			
Gate Resistance	R_{g}	f = 1 MHz		1.4	2.1	Ω	
Turn-On Delay Time	t _{d(on)}			18	27		
Rise Time	t _r	$V_{DD} = 15 \text{ V}, R_1 = 0.625 \Omega$		11	17	ns	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 24 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$		70	105		
Fall Time	t _f			10	15		
Turn-On Delay Time	t _{d(on)}			55	83		
Rise Time	t _r	$V_{DD} = 15 \text{ V}, R_{L} = 0.67 \Omega$		180	270		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 22.5 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_q = 1 \Omega$		55	83		
Fall Time	t _f	Ŭ		12	18		
Drain-Source Body Diode Characteristic				<u> </u>			
Continuous Source-Drain Diode Current	Is	T _C = 25 °C			120		
Pulse Diode Forward Current ^a	I _{SM}				120	A	
Body Diode Voltage	V _{SD}	I _S = 22 A		0.8	1.2	V	
Body Diode Reverse Recovery Time	t _{rr}	-		52	78	ns	
Body Diode Reverse Recovery Charge	Q _{rr}			70.2	105	nC	
Reverse Recovery Fall Time	t _a	$I_F = 20 \text{ A, di/dt} = 100 \text{ A/}\mu\text{s, T}_J = 25 ^{\circ}\text{C}$		27			
Reverse Recovery Rise Time	t _b			25		ns	

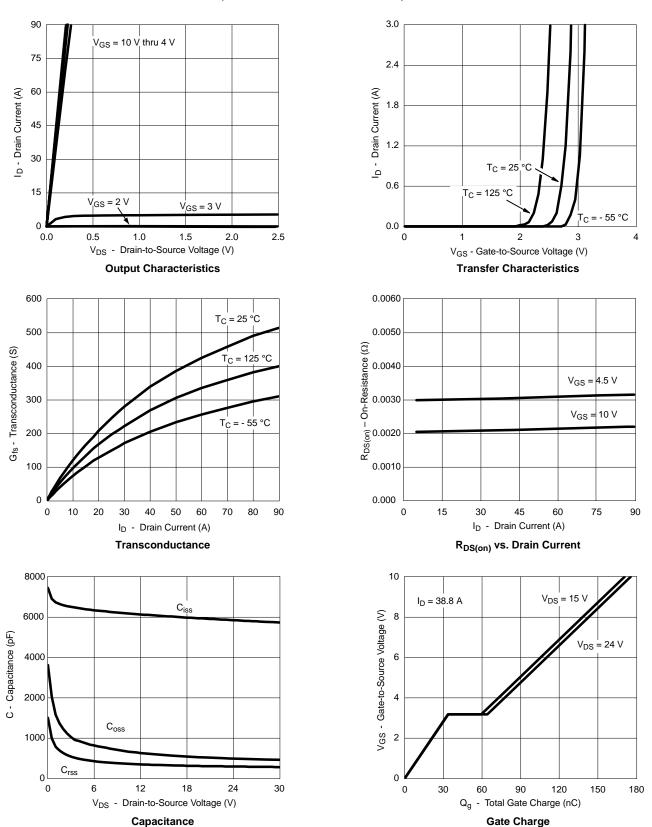
Notes:

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

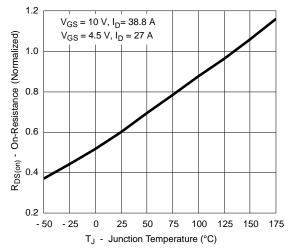


TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

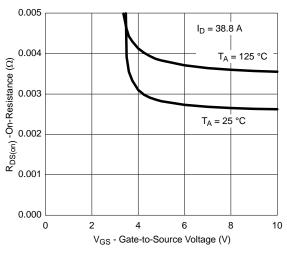




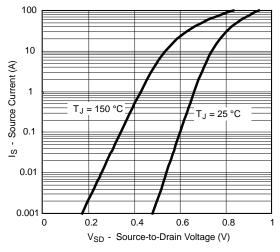
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



On-Resistance vs. Junction Temperature



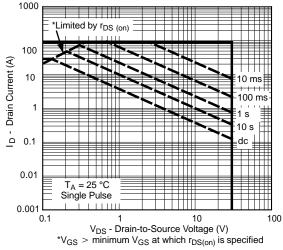
 $R_{DS(on)}$ vs. V_{GS} vs. Temperature



Forward Diode Voltage vs. Temperature



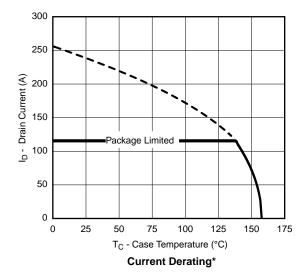
Threshold Voltage

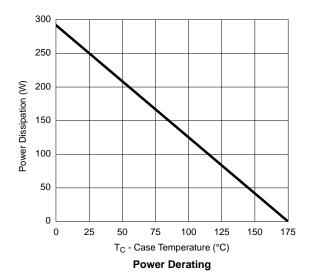


Safe Operating Area, Junction-to-Ambient

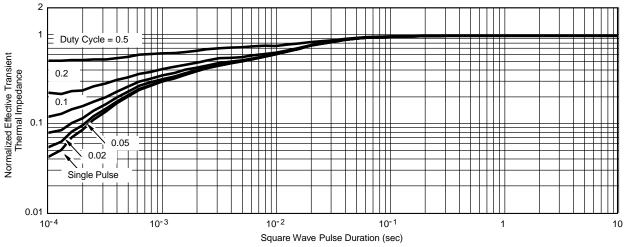


TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)





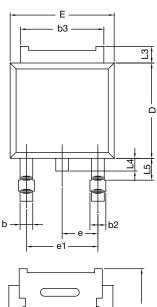
*The power dissipation P_D is based on $T_{J(max)}$ = 175 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

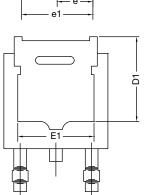


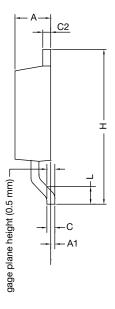
Normalized Thermal Transient Impedance, Junction-to-Case



TO-252AA CASE OUTLINE







	MILLIMETERS		INC	HES		
DIM.	MIN.	MAX.	MIN.	MAX.		
А	2.18	2.38	0.086	0.094		
A1	-	0.127	-	0.005		
b	0.64	0.88	0.025	0.035		
b2	0.76	1.14	0.030	0.045		
b3	4.95	5.46	0.195	0.215		
С	0.46	0.61	0.018	0.024		
C2	0.46	0.89	0.018	0.035		
D	5.97	6.22	0.235	0.245		
D1	5.21	-	0.205	-		
E	6.35	6.73	0.250	0.265		
E1	4.32	-	0.170	-		
Н	9.40	10.41	0.370	0.410		
е	2.28	8 BSC 0.090 BS		BSC		
e1	4.56 BSC		0.180 BSC			
L	1.40	1.78	0.055	0.070		
L3	0.89	1.27	0.035	0.050		
L4	-	1.02	-	0.040		
L5	1.14	1.52	0.045	0.060		
ECN: X12-0247-Rev. M, 24-Dec-12						

DWG: 5347

Note

• Dimension L3 is for reference only.



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